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APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.
10/711,640	09/29/2004	Basanth Jagannathan	FIS920040085	5639
45988 7590 03/29/2007 GREENBLUM & BERNSTEIN, P.L.C. 1950 ROLAND CLARKE PLACE RESTON, VA 20191			EXAMINER NGUYEN, TRAM HOANG	
			ART UNIT	PAPER NUMBER
			2818	
SHORTENED STATUTORY PERIOD OF RESPONSE		NOTIFICATION DATE	DELIVERY MODE	
3 MONTHS		03/29/2007	ELECTRONIC	

Please find below and/or attached an Office communication concerning this application or proceeding.

If NO period for reply is specified above, the maximum statutory period will apply and will expire 6 MONTHS from the mailing date of this communication.

Notice of this Office communication was sent electronically on the above-indicated "Notification Date" and has a shortened statutory period for reply of 3 MONTHS from 03/29/2007.

Notice of the Office communication was sent electronically on above-indicated "Notification Date" to the following e-mail address(es):

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Office Action Summary

Application No.

10/711,640

Applicant(s)

JAGANNATHAN ET AL.

Examiner

Tram H. Nguyen

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-- The MAILING DATE of this communication appears on the cover sheet with the correspondence address --
Period for Reply

A SHORTENED STATUTORY PERIOD FOR REPLY IS SET TO EXPIRE 3 MONTH(S) OR THIRTY (30) DAYS, WHICHEVER IS LONGER, FROM THE MAILING DATE OF THIS COMMUNICATION.

- Extensions of time may be available under the provisions of 37 CFR 1.136(a). In no event, however, may a reply be timely filed after SIX (6) MONTHS from the mailing date of this communication.
- If NO period for reply is specified above, the maximum statutory period will apply and will expire SIX (6) MONTHS from the mailing date of this communication.
- Failure to reply within the set or extended period for reply will, by statute, cause the application to become ABANDONED (35 U.S.C. § 133). Any reply received by the Office later than three months after the mailing date of this communication, even if timely filed, may reduce any earned patent term adjustment. See 37 CFR 1.704(b).

Status

- 1) ☒ Responsive to communication(s) filed on 20 December 2006.
2a) ☒ This action is **FINAL**. 2b) ☐ This action is non-final.
3) ☐ Since this application is in condition for allowance except for formal matters, prosecution as to the merits is closed in accordance with the practice under *Ex parte Quayle*, 1935 C.D. 11, 453 O.G. 213.

Disposition of Claims

- 4) ☒ Claim(s) 14-20 and 31-43 is/are pending in the application.
4a) Of the above claim(s) _____ is/are withdrawn from consideration.
5) ☐ Claim(s) _____ is/are allowed.
6) ☒ Claim(s) 14-20 and 31-43 is/are rejected.
7) ☐ Claim(s) _____ is/are objected to.
8) ☐ Claim(s) _____ are subject to restriction and/or election requirement.

Application Papers

- 9) ☐ The specification is objected to by the Examiner.
10) ☐ The drawing(s) filed on _____ is/are: a) ☐ accepted or b) ☐ objected to by the Examiner.
Applicant may not request that any objection to the drawing(s) be held in abeyance. See 37 CFR 1.85(a).
Replacement drawing sheet(s) including the correction is required if the drawing(s) is objected to. See 37 CFR 1.121(d).
11) ☐ The oath or declaration is objected to by the Examiner. Note the attached Office Action or form PTO-152.

Priority under 35 U.S.C. § 119

- 12) ☐ Acknowledgment is made of a claim for foreign priority under 35 U.S.C. § 119(a)-(d) or (f).
a) ☐ All b) ☐ Some * c) ☐ None of:
1. ☐ Certified copies of the priority documents have been received.
2. ☐ Certified copies of the priority documents have been received in Application No. _____.
3. ☐ Copies of the certified copies of the priority documents have been received in this National Stage application from the International Bureau (PCT Rule 17.2(a)).

* See the attached detailed Office action for a list of the certified copies not received.

Attachment(s)

- 1) ☒ Notice of References Cited (PTO-892)
2) ☐ Notice of Draftsperson's Patent Drawing Review (PTO-948)
3) ☐ Information Disclosure Statement(s) (PTO/SB/08)
Paper No(s)/Mail Date _____.
4) ☐ Interview Summary (PTO-413)
Paper No(s)/Mail Date _____.
5) ☐ Notice of Informal Patent Application
6) ☐ Other: _____.

DETAILED ACTION

In response to the communications dated 01/19/2007, claims 14-20,31-43 are pending in this application.

Claim Rejections - 35 USC § 102

The following is a quotation of the appropriate paragraphs of 35 U.S.C. 102 that form the basis for the rejections under this section made in this Office action:

A person shall be entitled to a patent unless –

(e) the invention was described in (1) an application for patent, published under section 122(b), by another filed in the United States before the invention by the applicant for patent or (2) a patent granted on an application for patent by another filed in the United States before the invention by the applicant for patent, except that an international application filed under the treaty defined in section 351(a) shall have the effects for purposes of this subsection of an application filed in the United States only if the international application designated the United States and was published under Article 21(2) of such treaty in the English language.

Claims 14,17, 31-33,36,40-43 are rejected under 35 U. S. C. § 102 (e) as being anticipated by Chen et al. (U.S. 2003/01977226) (hereinafter Chen).

Regarding **claim 14**, Chen discloses a semiconductor device (fig. 3) comprising:
a substrate (reference numeral 200); a source (reference numeral 208) and a drain (reference numeral 210) arranged within the substrate (reference numeral 200); gate (reference numeral 206) formed on the substrate (200) between the source and drain (208/210); and substrate contact (reference numeral 214) formed within the substrate in electrical contact with the source (Note: substrate contact 214 is electrically contact with the source 208 via the well 202), wherein little or no current flows through the

substrate contact (see fig. 3B).

Regarding **claim 17**, Chen discloses all the limitations of the claimed invention for the same reasons are set-forth above. In addition, Chen also teaches the substrate contact (214) comprises a p+ region (par. [0027], line 4).

Regarding **claim 31**, Chen discloses all the limitation of the claimed invention for the same reasons as set-forth above. Besides, fig. 3A shows the substrate contact (214) completely encircles an active region.

Regarding **claim 32**, Chen discloses all the limitations of the claimed invention for the same reasons as set-forth above. Besides, Chen teaches the semiconductor device comprises an FET prime cell (see fig. 3A).

Regarding **claim 33**, Chen discloses a semiconductor device (fig. 3B) comprising: a substrate (reference numeral 200); a source (reference numeral 14) and a drain (reference numeral 210) arranged within the substrate (reference numeral 200); a gate (206) formed on the substrate between the source and the drain (208/210); and a ring substrate contact (reference numeral 214) formed within the substrate in electrical contract with the source (fig. 3B).

Regarding **claim 36**, Chen discloses all the limitations of the claimed invention for the same reasons are set-forth above. In addition, Chen also teaches the substrate contact (214) comprises a p+ region (par. [0027], line 4).

Regarding **claim 40**, Chen discloses all the limitations of the claimed invention for the same reasons as set-forth above. Besides, Chen teaches the semiconductor device comprises an FET prime cell (see fig. 3A).

Regarding **claim 41**, Chen discloses all the limitation of the claimed invention for the same reasons as set-forth above. Besides, fig. 3A shows the substrate contact (214) completely encircles an active region.

Regarding **claim 42**, Chen discloses a semiconductor device (fig. 3B) comprising: a substrate (reference numeral 200); a source (reference numeral 14) and a drain (reference numeral 210) arranged within the substrate (reference numeral 200); a gate (206) formed on the substrate between the source and the drain (208/210); and a ring substrate contact (reference numeral 214) formed within the substrate in electrical contact with the source (fig. 3B), the substrate contact completely encircles an active region (see fig. 3A).

Regarding **claim 43**, Chen discloses all the limitations of the claimed invention for the same reasons as set-forth above. Besides, Chen teaches the semiconductor device comprises an FET prime cell (see fig. 3A).

Claim Rejections - 35 USC § 103

The following is a quotation of 35 U.S.C. 103(a) which forms the basis for all obviousness rejections set forth in this Office action:

(a) A patent may not be obtained though the invention is not identically disclosed or described as set forth in section 102 of this title, if the differences between the subject matter sought to be patented and the prior art are such that the subject matter as a whole would have been obvious at the time the invention was made to a person having ordinary skill in the art to which said subject matter pertains. Patentability shall not be negated by the manner in which the invention was made.

This application currently names joint inventors. In considering patentability of the claims under 35 U.S.C. 103(a), the examiner presumes that the subject matter of the various claims was commonly owned at the time any inventions covered therein

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were made absent any evidence to the contrary. Applicant is advised of the obligation under 37 CFR 1.56 to point out the inventor and invention dates of each claim that was not commonly owned at the time a later invention was made in order for the examiner to consider the applicability of 35 U.S.C. 103(c) and potential 35 U.S.C. 102(e), (f) or (g) prior art under 35 U.S.C. 103(a).

Claims 15,34 are rejected under 35 U.S.C. 103(a) as being unpatentable over Chen.

Regarding **claim 15**, Chen discloses all the limitations of the claimed invention for the same reasons as set-forth above. The recitation "the substrate contact being configured to shield the semiconductor device from electrical noise", refers to an operational limitation and any such limitation must distinguish from the prior art in terms of structure rather than function, *In re Schreiber*, 128 F.3d 1473, 1477-78, 44 USPQ2d 1429, 1431-32 (Fed. Cir. 1997); See also *In re Swinehart*, 439 F.2d 210, 212-13, 169 USPQ 226, 228-29 (CCPA 1971; *In re Danly*, 263, F.2d 844, 847, 120 USPQ 528, 531 (CCPA 1959).

Regarding **claim 34**, Chen discloses all the limitations of the claimed invention for the same reasons are set-forth above. The recitation "the ring substrate contact being configured to shield the semiconductor device from electrical noise", refers to an operational limitation and any such limitation must distinguish from the prior art in terms of structure rather than function, *In re Schreiber*, 128 F.3d 1473, 1477-78, 44 USPQ2d 1429, 1431-32 (Fed. Cir. 1997); See also *In re Swinehart*, 439 Fo2d210, 212-13, 169

USPQ 226,228-29 (CCPA 1971; In re Danly, 263, F.2d 844, 847, 120 USPQ 528, 531 (CCPA 1959).

Claims 16,20,35,39 rejected under 35 U.S.C. 103(a) as being unpatentable over Chen as applied to claim 14 above, and further in view of Herzum et al. (US 2004/0238871; hereinafter Herzum).

Regarding **claim 16**, Chen discloses all the limitations of the claimed invention for the same reasons as set-forth above; except for the substrate contact being in direct physical contact with the source of the semiconductor device. However, Herzum has a similar structure (fig. 1A) wherein the substrate contact (12) being in direct physical contact with the source of the semiconductor device (14). Therefore, it would have been obvious to one having ordinary skill in the art at the time the invention was made to modify the semiconductor device structure as such the substrate contact being in direct physical contact with the source of the semiconductor device as taught by Herzum in the semiconductor device structure as disclosed by Chen so that it reduces the length of the device structure.

Regarding **claim 20**, Chen discloses all the limitations of the claimed invention for the same reasons as set-forth above; except for the substrate contact comprises a p-type doped silicon tab contacting source and silicide layer on a top of the substrate contact. However, Herzum has a similar structure wherein fig. 3 shows the substrate contact (reference numeral 12) comprises a p-type doped silicon tab contacting source (reference numeral 14) and a silicide layer (reference numeral 52) on a top of the

substrate contact (reference numeral 12). Therefore, it would have been obvious to one having ordinary skill in the art at the same time the invention was made to reduce the resistance.

Regarding **claim 35**, Chen discloses all the limitations of the claimed invention for the same reasons as set-forth above except for the substrate contact being in direct physical contact with the source of the semiconductor device. However, Herzum has a similar structure (fig. 1A) wherein the substrate contact (12) being in direct physical contact with the source of the semiconductor device (14). Therefore, it would have been obvious to one having ordinary skill in the art at the time the invention was made to modify the semiconductor device structure as such the substrate contact being in direct physical contact with the source of the semiconductor device as taught by Herzum in the semiconductor device structure as disclosed by Chen so that it reduces the length of the device structure.

Regarding **claim 39**, Chen discloses all the limitations of the claimed invention for the same reasons as set-forth above; except for the substrate contact comprises a p-type doped silicon tab contacting source and silicide layer on a top of the substrate contact. However, Herzum has a similar structure wherein fig. 3 shows the substrate contact (reference numeral 12) comprises a p-type doped silicon tab contacting source (reference numeral 14) and a silicide layer (reference numeral 52) on a top of the substrate contact (reference numeral 12). Therefore, it would have been obvious to one having ordinary skill in the art at the same time the invention was made to reduce the resistance.

Claims 18,19,37,38 are rejected under 35 U.S.C. 103(a) as being unpatentable over Chen as applied to claim 14 above, and further in view of Rice et al. (US 4,738,936; hereinafter Rice).

Regarding **claim 18**, Chen discloses all the limitations of the claimed invention for the same reasons as set-forth above except for the source comprises a source finger and the substrate contact abuts substantially all of one side of the source finger. However, Rice has a similar structure (fig. 1H) (Note: the current flows through the substrate contact (described in col. 4, lines 36-38) wherein the source comprises a source finger and the substrate contact (20) abuts all one side of the source finger (60) (col. 4, line 19). Therefore, it would have been obvious at the time the invention was made to a person having ordinary skill in the art to provide a source direct source to substrate contact in order to reduce expensive packaging techniques, further reduce output capacitance, and to reduce or eliminate junction capacitance (col.1, lines 56-59).

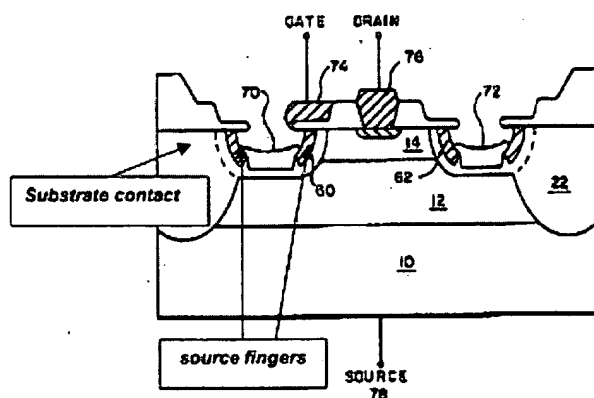


FIG. -1H

Regarding **claim 19**, Chen and Rice disclose all the limitations of the claimed invention for the same reasons as set-forth above; likewise, Rice also teaches two

source fingers arranged within substrate, wherein the substrate contact abuts two of the two source fingers (refer the above fig. 1H).

Regarding **claim 37**, Chen discloses all the limitation of the claimed invention for the same reasons as set-forth above except for the source comprises a source finger and the substrate contact abuts substantially all of one side of the source finger. However, Rice has a similar structure (fig. 1H) (Note: the current flows through the ring substrate contact (described in col. 4, lines 36-38)) wherein the source comprises a source finger and the ring substrate contact (reference numeral 20) abuts all of one side of the source finger (reference numeral 60) (col. 4, line 19). Therefore, it would have been obvious at the time the invention was made to a person having ordinary skill in the art to provide a source direct source to substrate contact in order to reduce expensive packaging techniques, further reduce output capacitance, and to reduce or eliminate junction capacitance (col.1, lines 56-59).

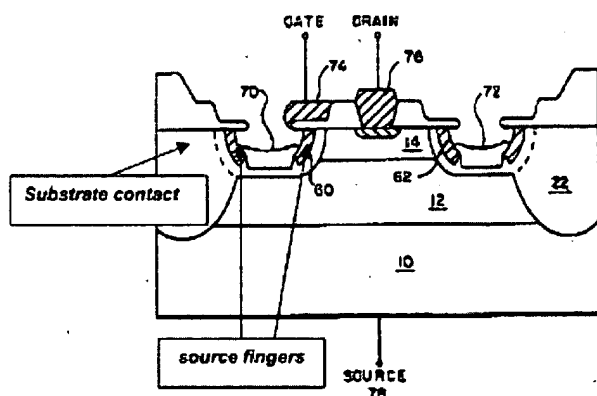


FIG. 1H

Regarding **claim 38**, Chen and Rice disclose all the limitations of the claimed invention for the same reasons are set-forth above; likewise, Rice also teaches two

source fingers arranged within substrate, wherein the substrate contact abuts two of the two source fingers (refer the above fig. 1H).

Response to Arguments

Applicant's arguments filed 12/20/2006 have been fully considered. The transversal is on the ground(s) that "HERZUM cannot be read to disclose that little or no current flows through the substrate contact." But they are not persuasive. Examiner admits that par.[0036] does not teach little or no current flows through the substrate. However, sinker 12 is not applied with any potential. Therefore, no current should flow through the substrate contact.

Conclusion

Applicant's amendment necessitated the new ground(s) of rejection presented in this Office action. Accordingly, **THIS ACTION IS MADE FINAL**. See MPEP § 706.07(a). Applicant is reminded of the extension of time policy as set forth in 37 CFR 1.136(a).

A shortened statutory period for reply to this final action is set to expire **THREE MONTHS** from the mailing date of this action. In the event a first reply is filed within **TWO MONTHS** of the mailing date of this final action and the advisory action is not mailed until after the end of the **THREE-MONTH** shortened statutory period, then the shortened statutory period will expire on the date the advisory action is mailed, and any extension fee pursuant to 37 CFR 1.136(a) will be calculated from the mailing date of

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the advisory action. In no event, however, will the statutory period for reply expire later than SIX MONTHS from the date of this final action.

Any inquiry concerning this communication or earlier communications from the examiner should be directed to Tram Hoang Nguyen whose telephone number is (571)272-5526. The examiner can normally be reached on Monday-Friday, 8:30 AM – 5:00 PM. If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Mathew Smith can be reached on (571)272-1907. The fax numbers for all communication(s) is (703)872-9306.

Any inquiry of a general nature or relating to the status of this application or proceeding should be directed to the receptionist whose telephone number is (571)272-1625.

THN
Art Unit 2818
03/18/2007

Andy Hung
Andy Hung
Primary Examiner